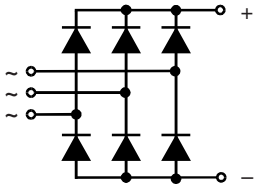
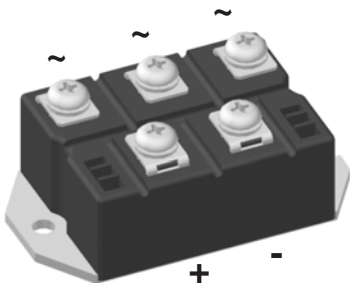
Three Phase Rectifier Bridge

I_{dAV} = 248 A
V_{RRM} = 800-1800 V

V_{RSM} V	V_{RRM} V	Type
800	800	VUO 190-08NO7
1200	1200	VUO 190-12NO7
1400	1400	VUO 190-14NO7
1600	1600	VUO 190-16NO7
1800	1800	VUO 190-18NO7*

* delivery time on request





Symbol	Test Conditions		Maximum Ratings	
I_{dAV}	T_C = 90°C, module		248	A
I_{dAV}	T_A = 35°C (R_{thCA} = 0.2 K/W), module		165	A
I_{FSM}	T_{VJ} = 45°C;	t = 10 ms (50 Hz), sine	2800	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	3300	A
	T_{VJ} = T_{VJM}	t = 10 ms (50 Hz), sine	2500	A
	V_R = 0	t = 8.3 ms (60 Hz), sine	2750	A
I^2t	T_{VJ} = 45°C	t = 10 ms (50 Hz), sine	39 200	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	45 000	A^2s
	T_{VJ} = T_{VJM}	t = 10 ms (50 Hz), sine	31 200	A^2s
	V_R = 0	t = 8.3 ms (60 Hz), sine	31 300	A^2s
T_{VJ}			-40...+150	°C
T_{VJM}			150	°C
T_{stg}			-40...+125	°C
V_{ISOL}	50/60 Hz, RMS	t = 1 min	2500	V~
	I_{ISOL} ≤ 1 mA	t = 1 s	3000	V~
M_d	Mounting torque (M6)		5 ± 15 %	Nm
	Terminal connection torque (M6)		5 ± 15 %	Nm
Weight	typ.		270	g

Symbol	Test Conditions		Characteristic Values		
I_R	V_R = V_{RRM};	T_{VJ} = 25°C	≤	0.3	mA
	V_R = V_{RRM};	T_{VJ} = T_{VJM}	≤	5	mA
V_F	I_F = 300 A;	T_{VJ} = 25°C	≤	1.43	V
V_{T0}	For power-loss calculations only			0.8	V
r_T				2.2	mΩ
R_{thJC}	per diode, 120°			0.45	K/W
	per module			0.075	K/W
R_{thJH}	per diode, 120°			0.6	K/W
	per module			0.1	K/W
d_S	Creeping distance on surface			10	mm
d_A	Creepage distance in air			9.4	mm
a	Max. allowable acceleration			50	m/s^2

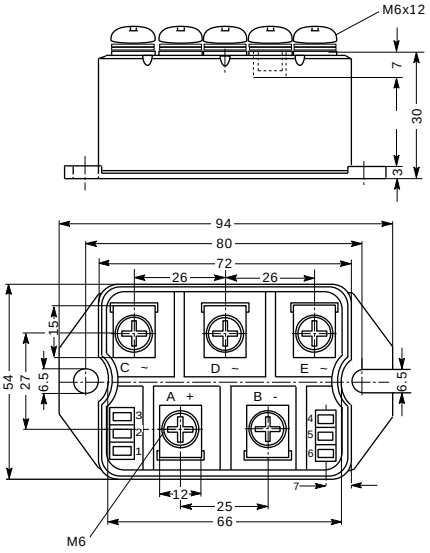
Data according to IEC 60747 and refer to a single diode unless otherwise stated.

Features
- Package with screw terminals
- Isolation voltage 3000 V~
- Planar passivated chips
- Blocking voltage up to 1800 V
- Low forward voltage drop
- UL registered E72873

Applications
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages
- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling

Dimensions in mm (1 mm = 0.0394")



IXYS reserves the right to change limits, test conditions and dimensions.

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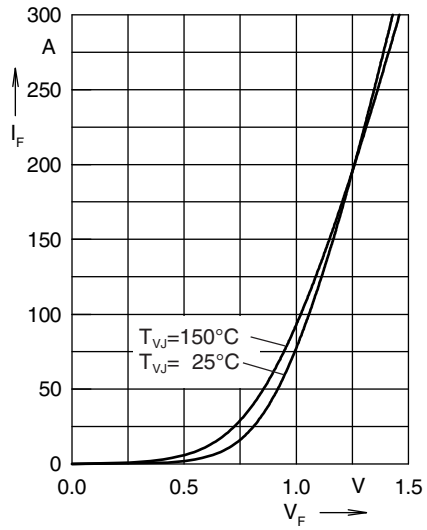

Fig. 4 Forward current versus voltage drop per diode

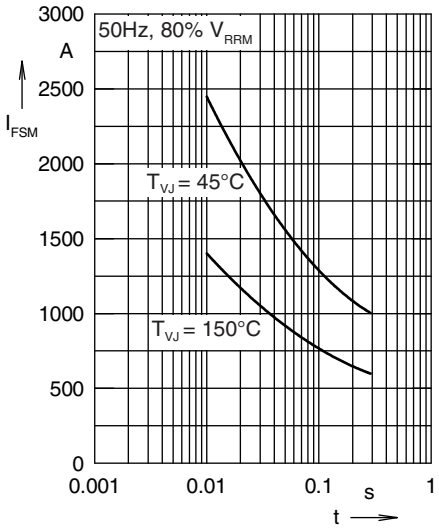

Fig. 5 Surge overload current

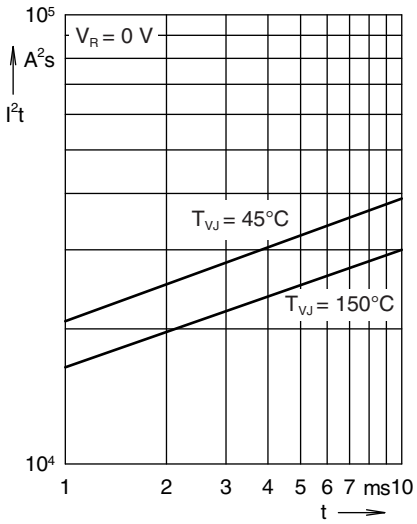

Fig. 6 I^2t versus time per diode

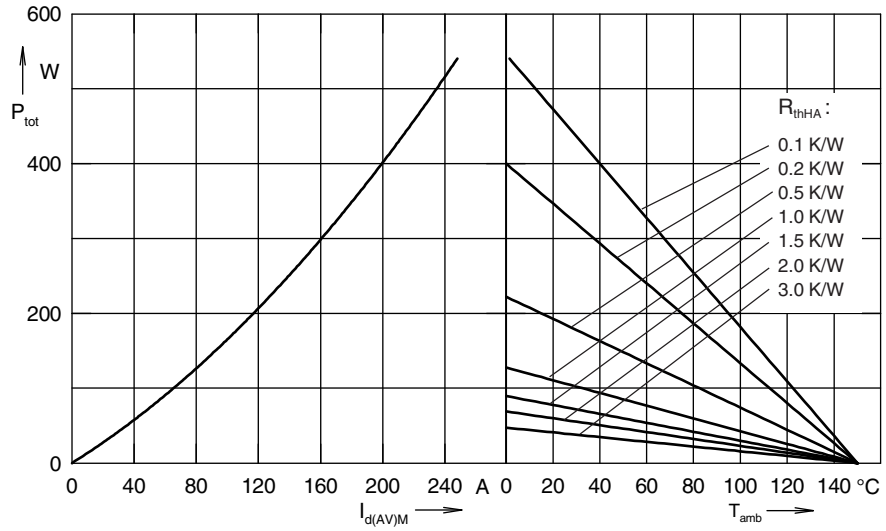

Fig. 7 Power dissipation versus direct output current and ambient temperature

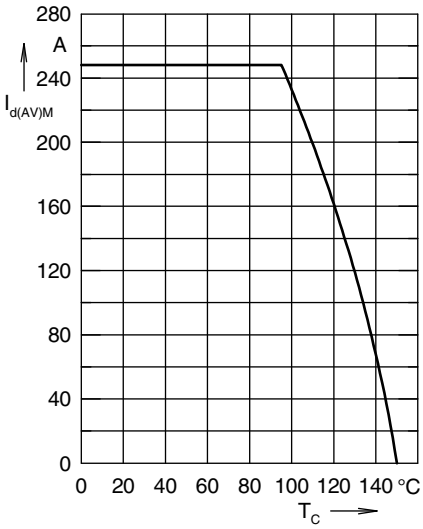

Fig. 8 Max. forward current versus case temperature

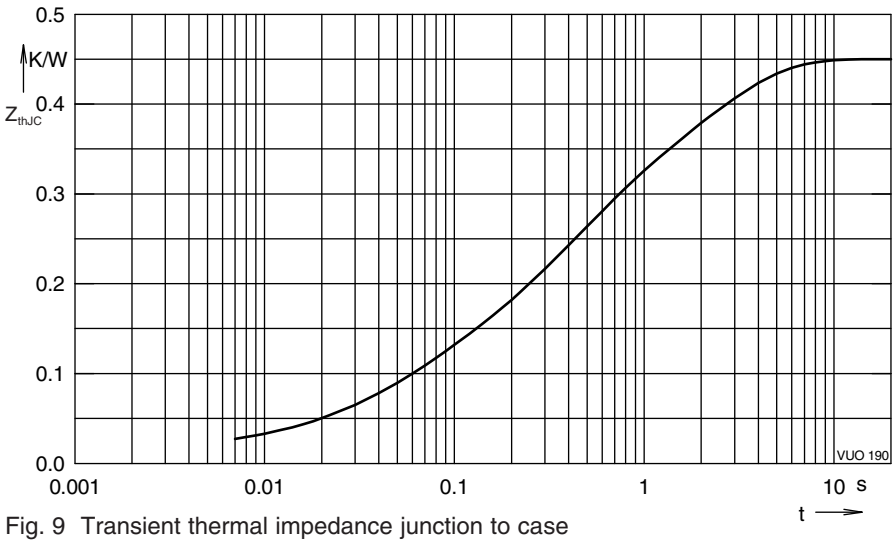

Fig. 9 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.013	0.0012
2	0.072	0.047
3	0.175	0.326
4	0.19	2.03